

# BT1308-400D/600D

Logic level triac

Rev. 01 — 19 February 2004

Product data

## 1. Product profile

### 1.1 Description

Logic level sensitive gate triac intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

### 1.2 Features

- Sensitive gate in all four quadrants
- Low cost package.

### 1.3 Applications

- General purpose bidirectional switching
- Solid state relays
- Phase control applications
- Low power AC fan speed controllers.

### 1.4 Quick reference data

- $V_{DRM} \leq 600$  V (BT1308-600D)
- $V_{DRM} \leq 400$  V (BT1308-400D)
- $I_{TSM} \leq 9$  A
- $I_{T(RMS)} \leq 0.8$  A.

## 2. Pinning information

Table 1: Pinning - SOT54 (TO-92), simplified outline and symbol

Pin	Description	Simplified outline	Symbol
1	main terminal 2		
2	gate		
3	main terminal 1		

MSB033  
SOT54 (TO-92)  
MBL305



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### 3. Ordering information

Table 2: Ordering information

Type number	Package		Version
	Name	Description	
BT1308-600D	TO-92	Plastic single-ended leaded (through hole) package; 3 leads	SOT54
BT1308-400D	TO-92	Plastic single-ended leaded (through hole) package; 3 leads	SOT54

### 4. Limiting values

Table 3: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
$V_{\text{DRM}}$	repetitive peak off-state voltage					
		BT1308-600D	$25\text{ °C} \leq T_j \leq 125\text{ °C}$	-	600	V
		BT1308-400D		-	400	V
$I_{\text{T(RMS)}}$	on-state current (RMS value)	full sine wave; $T_{\text{lead}} \leq 55\text{ °C}$ ; <b>Figure 1 and 2</b>	-	0.8	A	
$I_{\text{TSM}}$	non-repetitive peak on-state current	full sine wave; $T_j = 25\text{ °C}$ prior to surge; <b>Figure 3 and 4</b>				
		$t = 20\text{ ms}$	-	9	A	
		$t = 16.7\text{ ms}$	-	10	A	
$I^2t$	$I^2t$ for fusing	$t = 10\text{ ms}$	-	0.32	$\text{A}^2\text{s}$	
$di_T/dt$	repetitive rate of rise of on-state current after triggering	$I_{\text{TM}} = 1\text{ A}$ ; $I_{\text{G}} = 0.2\text{ A}$ ; $di_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$				
		T2+ G+	-	50	$\text{A}/\mu\text{s}$	
		T2+ G-	-	50	$\text{A}/\mu\text{s}$	
		T2- G-	-	50	$\text{A}/\mu\text{s}$	
		T2- G+	-	10	$\text{A}/\mu\text{s}$	
$I_{\text{GM}}$	gate current (peak value)	$t = 2\text{ }\mu\text{s max}$	-	1	A	
$V_{\text{GM}}$	gate voltage (peak value)		-	5	V	
$P_{\text{GM}}$	gate power (peak value)		-	5	W	
$P_{\text{G(AV)}}$	average gate power	$t = 2\text{ }\mu\text{s max}$ ; $T_{\text{case}} \leq 80\text{ °C}$	-	0.1	W	
$T_{\text{stg}}$	storage temperature		-40	+150	$^{\circ}\text{C}$	
$T_j$	junction temperature		-40	+125	$^{\circ}\text{C}$	

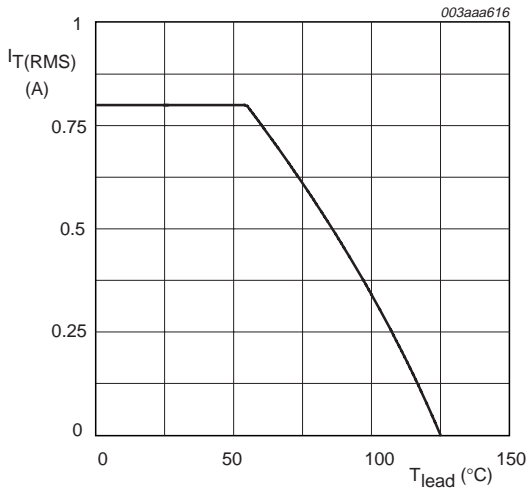
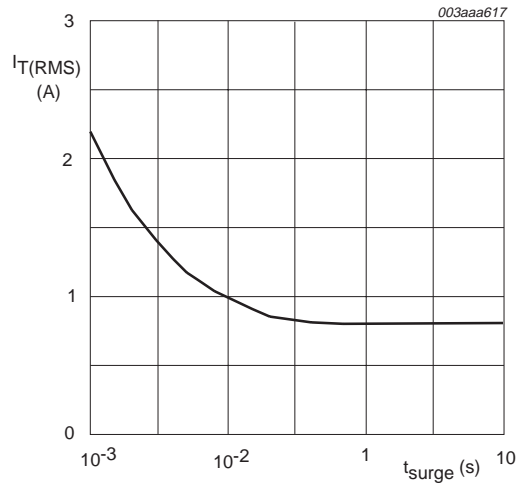
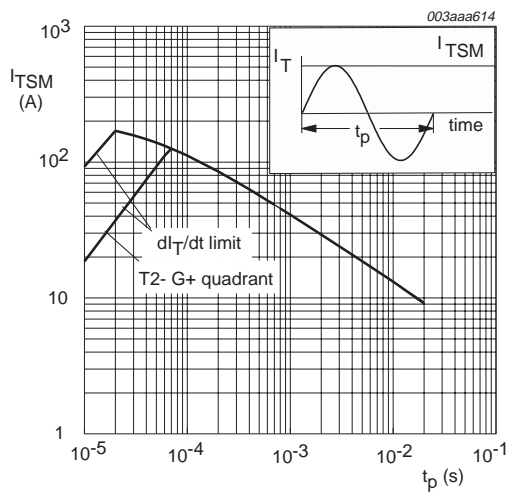


Fig 1. Maximum permissible on-state current (RMS value) as a function of lead temperature.



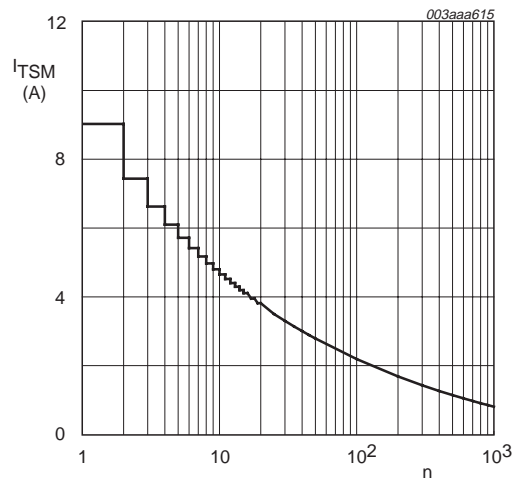
$f = 50 \text{ Hz}$   
 $T_{\text{lead}} \leq 65 \text{ }^{\circ}\text{C}$

Fig 2. Maximum permissible repetitive on-state current (RMS value) as a function of surge duration for sinusoidal currents.



$t_p \leq 20 \text{ ms}$   
 initial  $T_j \leq 25 \text{ }^{\circ}\text{C}$

Fig 3. Maximum permissible non-repetitive peak on-state current as a function of pulse width for sinusoidal currents.



$n = \text{number of cycles}$   
 $f = 50 \text{ Hz}$   
 initial  $T_j \leq 25 \text{ }^{\circ}\text{C}$

Fig 4. Maximum permissible non-repetitive peak on-state current as a function of number of cycles for sinusoidal currents.

## 5. Thermal characteristics

Table 4: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-lead)}$	thermal resistance from junction to lead	full cycle	-	-	60	K/W
		half cycle			80	
$R_{th(j-a)}$	thermal resistance from junction to ambient	mounted on a printed-circuit board; lead length = 4 mm; <b>Figure 5</b>	-	150	-	K/W

### 5.1 Transient thermal impedance

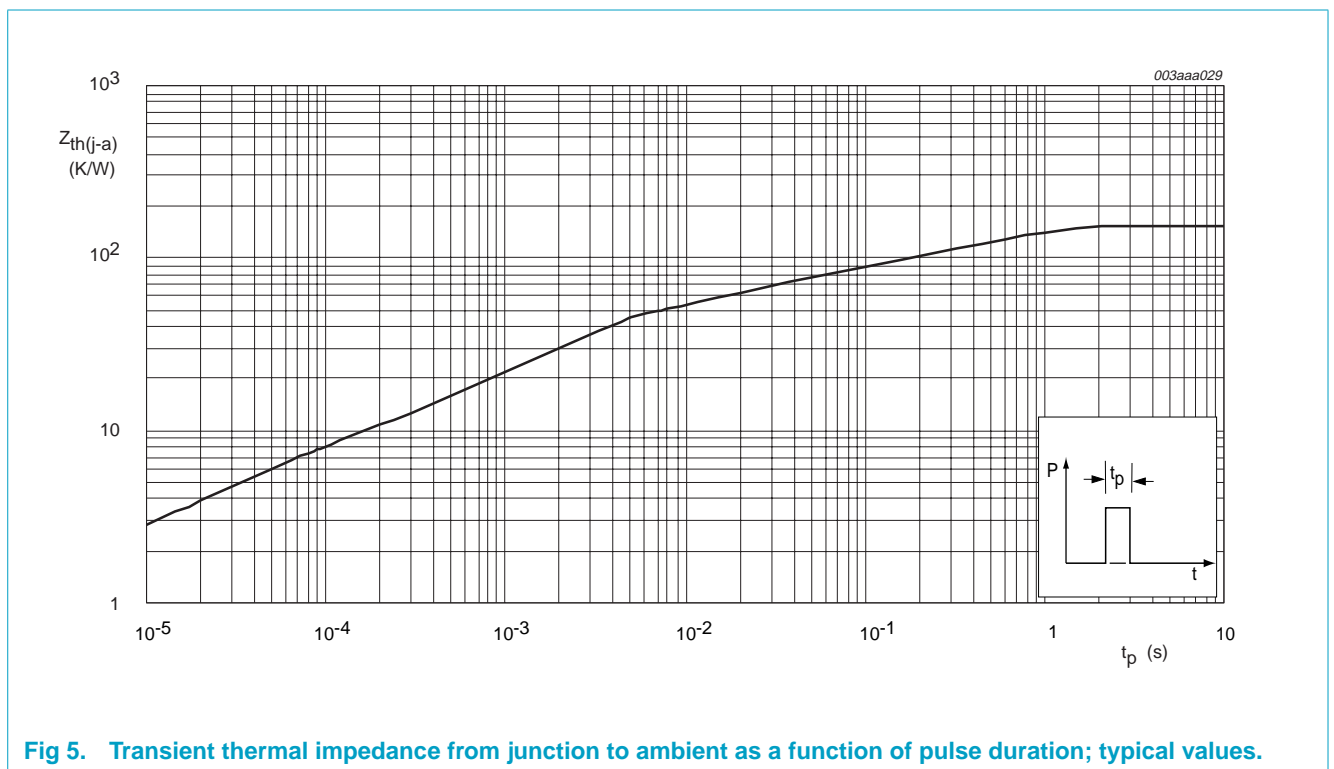


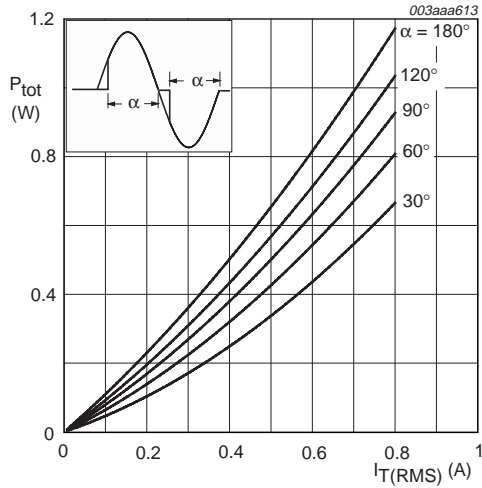
Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values.

## 6. Characteristics

**Table 5: Characteristics**

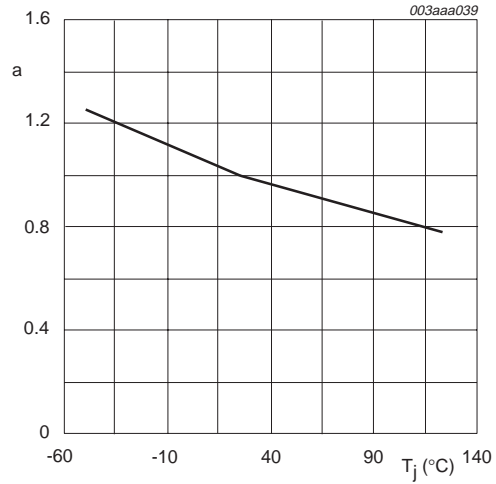
$T_j = 25\text{ °C}$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; <b>Figure 8</b>				
		T2+ G+	-	1	5	mA
		T2+ G-	-	2	5	mA
		T2- G-	-	2	5	mA
		T2- G+	-	4	7	mA
$I_L$	latching current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; <b>Figure 9</b>				
		T2+ G+	-	1	10	mA
		T2+ G-	-	5	10	mA
		T2- G-	-	1	10	mA
		T2- G+	-	2	10	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $I_{GT} = 0.1\text{ A}$ ; <b>Figure 10</b>	-	1	10	mA
$V_T$	on-state voltage	$I_T = 0.85\text{ A}$ ; <b>Figure 11</b>	-	1.35	1.6	V
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; <b>Figure 7</b>	-	0.9	2	V
		$V_D = V_{DRM}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 110\text{ °C}$	0.1	0.7	-	V
$I_D$	off-state leakage current	$V_D = V_{DRM(max)}$ ; $T_j = 110\text{ °C}$	-	3	100	$\mu\text{A}$
<b>Dynamic characteristics</b>						
$dV_D/dt$	critical rate of rise of off-state voltage	$V_D = 67\%$ of $V_{DM(max)}$ ; $T_{case} = 110\text{ °C}$ ; exponential waveform; gate open circuit; <b>Figure 12</b>	30	45	-	$\text{V}/\mu\text{s}$
$dV_{com}/dt$	critical rate of rise of commutation voltage	$V_D = \text{rated } V_{DM}$ ; $T_{case} = 50\text{ °C}$ ; $I_{TM} = 0.84\text{ A}$ ; commutating $di/dt = 0.3\text{ A/ms}$	-	5	-	$\text{V}/\mu\text{s}$
$t_{gt}$	gate controlled turn-on time	$I_{TM} = 1.0\text{ A}$ ; $V_D = V_{DRM(max)}$ ; $I_G = 25\text{ mA}$ ; $di_G/dt = 5\text{ A}/\mu\text{s}$	-	2	-	$\mu\text{s}$



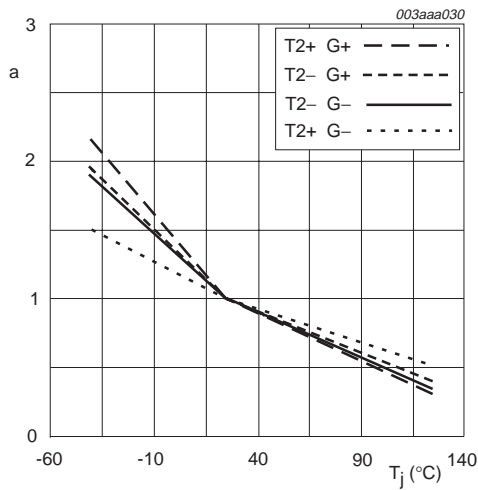
$\alpha$  = conduction angle

Fig 6. On-state dissipation as a function of on-state current (RMS value); maximum values.



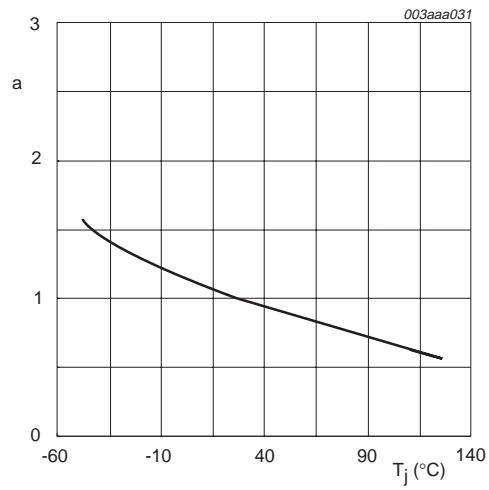
$$a = \frac{V_{GT}(T_j)}{V_{GT}(25^\circ\text{C})}$$

Fig 7. Normalized gate trigger voltage as a function of junction temperature; typical values.



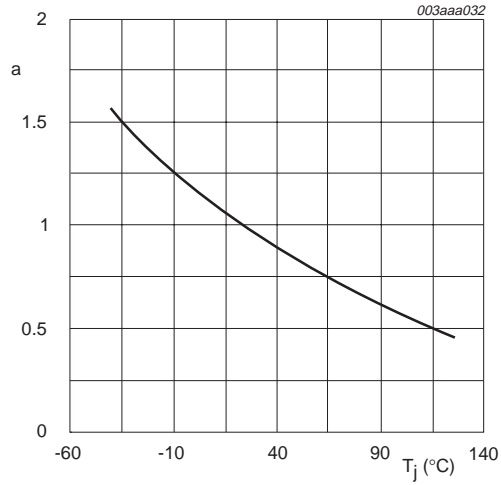
$$a = \frac{I_{GT}(T_j)}{I_{GT}(25^\circ\text{C})}$$

Fig 8. Normalized gate trigger current as a function of junction temperature; typical values.



$$a = \frac{I_L(T_j)}{I_L(25^\circ\text{C})}$$

Fig 9. Normalized latching current as a function of junction temperature; typical values.



$$a = \frac{I_{H(T_j)}}{I_{H(25^\circ C)}}$$

Fig 10. Normalized holding current as a function of junction temperature; typical values

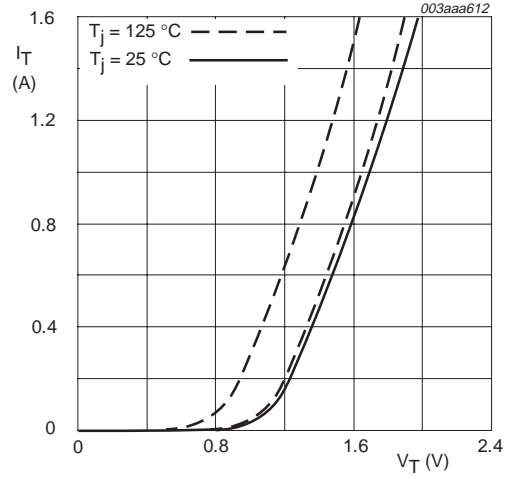


Fig 11. On-state current as a function of on-state voltage; typical and maximum values.

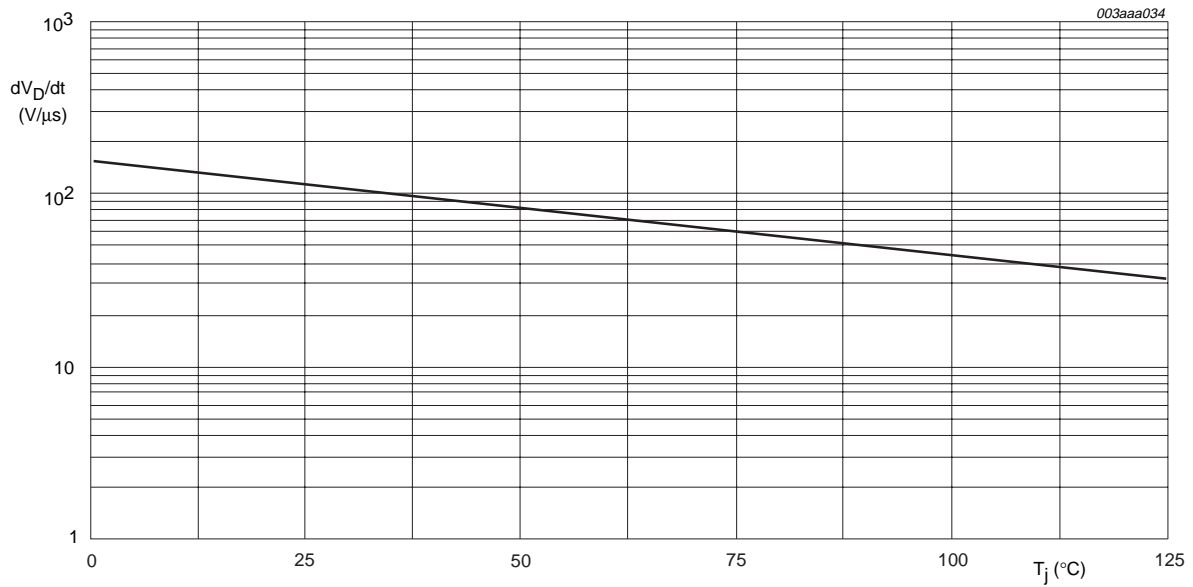


Fig 12. Critical rate of rise of off-state voltage as a function of junction temperature; typical values.

7. Package outline

Plastic single-ended leaded (through hole) package; 3 leads

SOT54

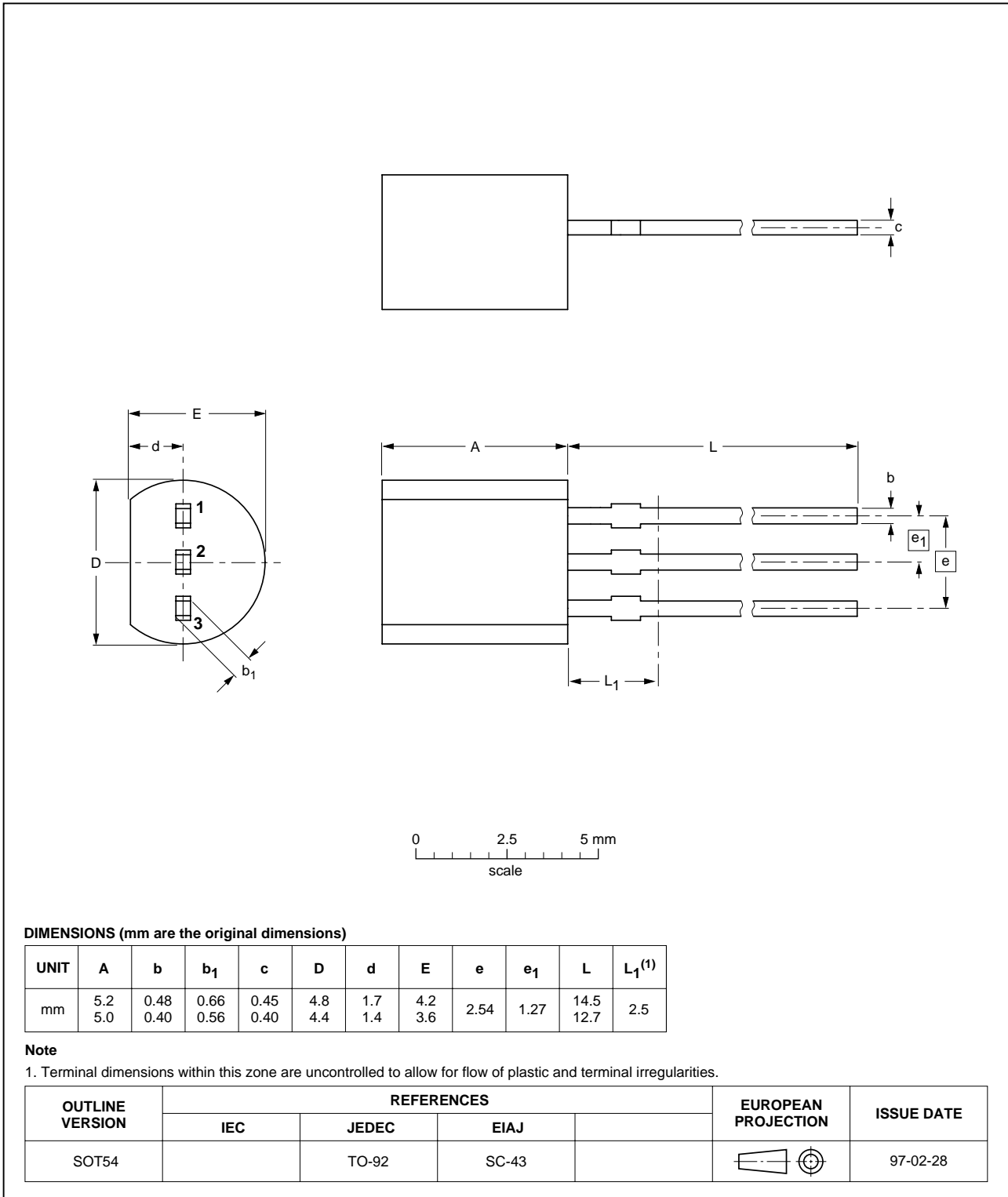


Fig 13. SOT54 (TO-92).



## 8. Revision history

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Table 6: Revision history

Rev	Date	CPCN	Description
01	20040219	-	Product data (9397 750 12594)

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## 9. Data sheet status

Level	Data sheet status <sup>[1]</sup>	Product status <sup>[2][3]</sup>	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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